IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Masahiko SANO et al.

Serial No. NEW

Filed July 9, 2003

A NITRIDE SEMICONDUCTOR ELEMENT WITH A SUPPORTING SUBSTRATE AND A METHOD FOR PRODUCING A NITRIDE SEMICONDUCTOR ELEMENT (Rule 1.53(b) Divisional of Serial No. 10/351,497, Filed January 27, 2003)

Attn: APPLICATION BRANCH

Attorney Docket No. 2003_0889

THE COMMISSIONER IS AUTHORIZED TO CHARGE ANY DEFICIENCY IN THE FREES FOR THIS PAPER TO DEPOSIT ACCOUNT NO. 23-0975

CLAIM OF PRIORITY UNDER 35 USC 119

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Applicants in the above-entitled application hereby claim the date of priority under the International Convention of Japanese Patent Application No. 19192/2002, filed January 28, 2002, Japanese Patent Application No. 195179/2002, filed July 3, 2002, Japanese Patent Application No. 356463/2002, filed December 9, 2002, Japanese Patent Application No. 175686/2002, filed June 17, 2002 and Japanese Patent Application No. 233866, filed August 9, 2002 as acknowledged in the Declaration of this application.

Respectfully submitted,

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